

Standard Rectifier Module

$$V_{RRM} = 1600\text{ V}$$

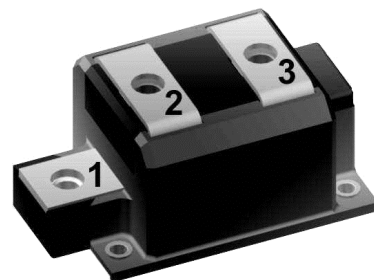
$$I_{FAV} = 2 \times 700\text{ A}$$

$$V_F = 1.05\text{ V}$$

Common Cathode

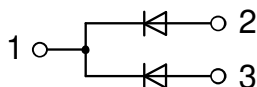
Part number

MDMA1400C1600CC



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: ComPack

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			500	μA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			20	mA
V_F	forward voltage drop	$I_F = 700\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.14	V
		$I_F = 1400\text{ A}$				1.35	V
		$I_F = 700\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.05	V
		$I_F = 1400\text{ A}$				1.30	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			700	A
$I_{F(RMS)}$	RMS forward current	rectangular $d = 0.5$				1100	A
V_{F0}	threshold voltage	for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					0.35	m Ω
R_{thJC}	thermal resistance junction to case					0.055	K/W
R_{thCH}	thermal resistance case to heatsink				0.02		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				2270	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			20.0	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			21.6	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			17.0	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			18.4	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.00	MA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.94	MA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.45	MA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.40	MA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}\text{C}$		781	pF

Package ComPack				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				1200	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					500		g
M_D	mounting torque			3		5	Nm
M_T	terminal torque			12		14	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal		21.0			mm
$d_{Spb/Apb}$		terminal to backside		18.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800			V
		t = 1 minute		4000			V



Part description

M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 1400 = Current Rating [A]
 C = Common Cathode
 1600 = Reverse Voltage [V]
 CC = ComPack

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA1400C1600CC	MDMA1400C1600CC	Box	3	520221

Equivalent Circuits for Simulation

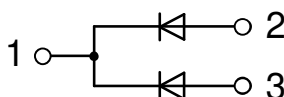
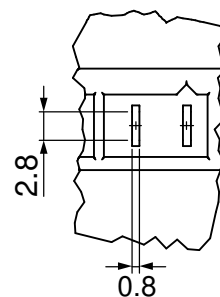
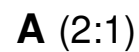
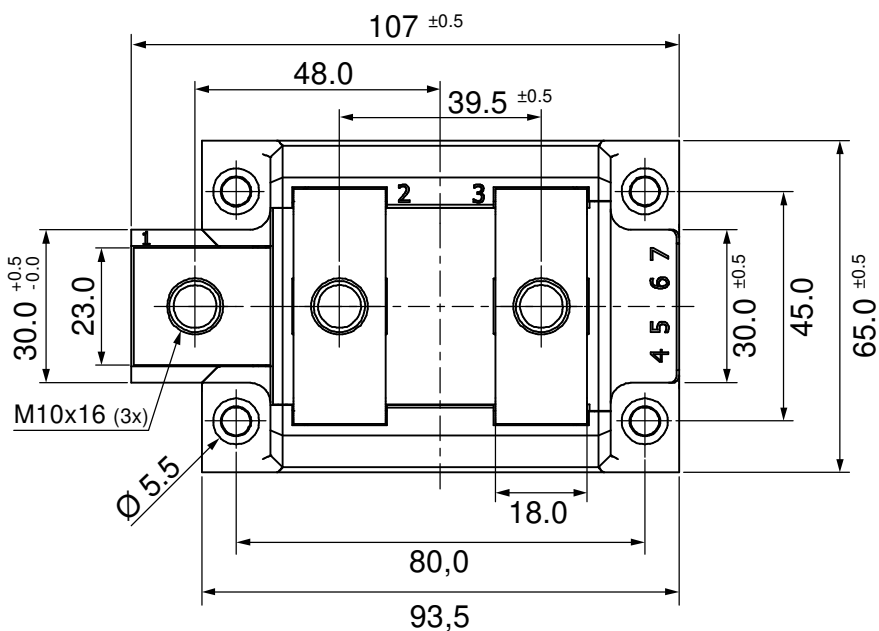
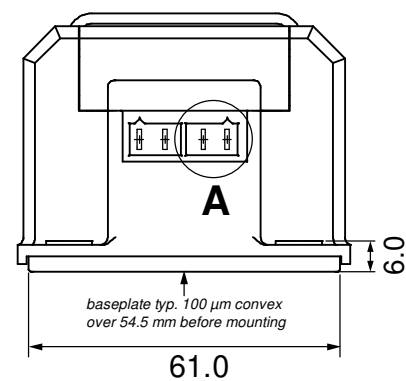
* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	0.16	mΩ

[illegible]

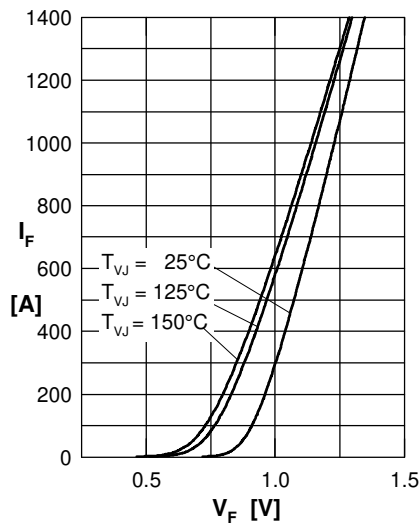
Rectifier


Fig. 1 Forward current versus voltage drop per diode

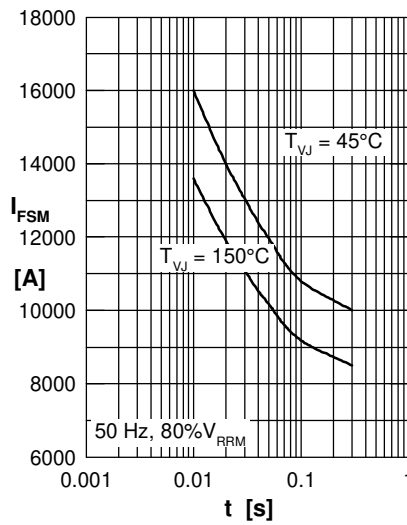


Fig. 2 Surge overload current vs. time per diode

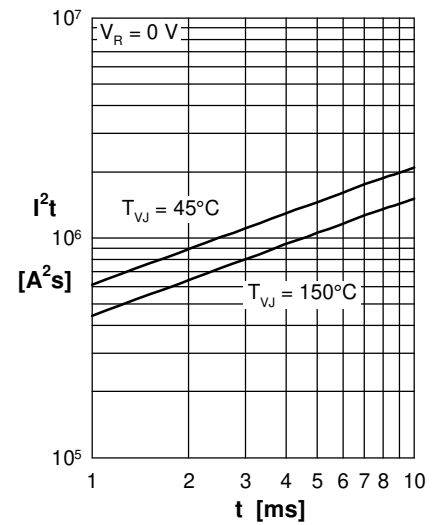
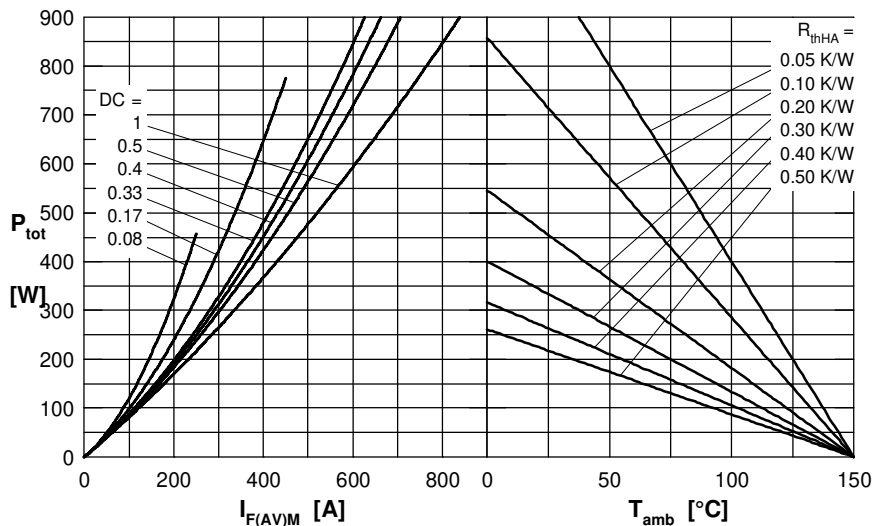

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

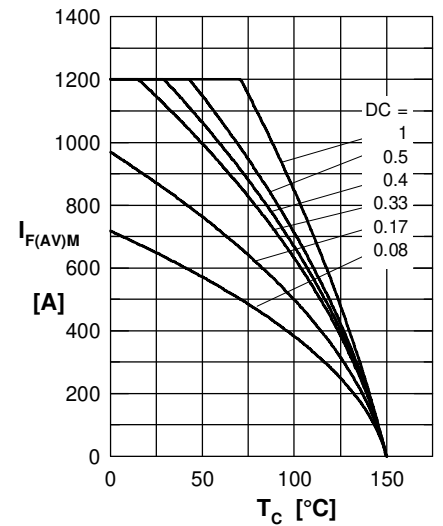


Fig. 5 Max. forward current vs. case temperature per diode

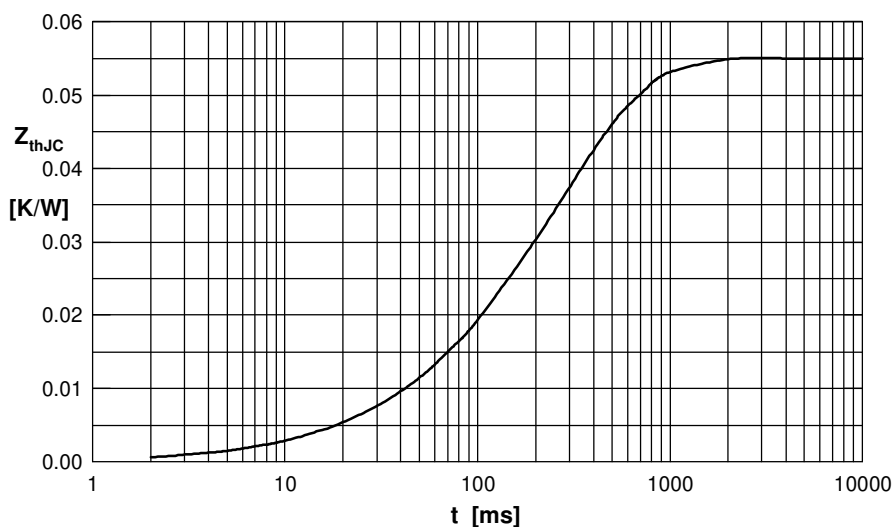


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.001	0.0150
2	0.004	0.0600
3	0.017	0.2000
4	0.033	0.3400